## 1. General description

Ultrafast dual epitaxial rectifier diode in a SOT78 (TO-220AB) plastic package.

### 2. Features and benefits

- High reverse voltage surge capability
- High thermal cycling performance
- Low thermal resistance
- Very low on-state loss
- · Soft recovery characteristic minimizes power consuming oscillations

## 3. Applications

· Output rectifiers in high-frequency switched-mode power supplies

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Va	lues		Unit
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage			1	00		V
$I_{O(AV)}$	average output current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 115$ °C; both diodes conducting; Fig. 1; Fig. 2		2	20		А
I <sub>RRM</sub>	repetitive peak reverse current	$\delta$ = 0.001; $t_p$ = 2 $\mu$ s;		(	).2		А
V <sub>ESD</sub>	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ; all pins	8				kV
I <sub>FRM</sub>	repetitive peak forward current	$δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_{mb} \le 115 °C$ ; per diode	20			А	
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	125				А
		$t_p$ = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	137			А	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>		-	0.72	0.85	V
Dynamic	characteristics				1	1	
t <sub>rr</sub> reverse recovery time		$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; ramp recovery; Fig. 5		-	20	25	ns
		$I_F = 0.5 \text{ A to } I_R = 1 \text{ A}; T_j = 25 ^{\circ}\text{C};$ measured at $I_R = 0.25 \text{ A};$ step recovery; Fig. 6		-	10	20	ns

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# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	
2	K	cathode	7 7	[5]
3	A2	anode 2		A1 A2
mb	К	mounting base; cathode		K sym125
			1 2 3	

## 6. Ordering information

**Table 3. Ordering information** 

Type number	Package		
	Name	Description	Version
BYV32E-100	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

# 7. Marking

Table 4. Marking codes

Type number	Marking codes
BYV32E-100	BYV32E-100

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# 8. Limiting values

### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		100	V
$V_{RWM}$	crest working reverse voltage		100	V
$V_R$	reverse voltage	DC	100	V
I <sub>O(AV)</sub>	average output current	δ = 0.5; square-wave pulse; T <sub>mb</sub> ≤ 115 °C; both diodes conducting; <u>Fig 1</u> ; <u>Fig 2</u>	20	А
I <sub>FRM</sub>	repetitive peak forward current	$δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_{mb} \le 115 °C$ ; per diode	20	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	125	А
		$t_p$ = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	137	А
I <sub>RRM</sub>	repetitive peak reverse current	$\delta$ = 0.001; $t_p$ = 2 $\mu$ s; per diode	0.2	А
I <sub>RSM</sub>	non-repetitive peak reverse current	t <sub>p</sub> = 100 μs; per diode	0.2	Α
T <sub>stg</sub>	storage temperature		-40 to 150	°C
T <sub>j</sub>	junction temperature		150	°C
V <sub>ESD</sub>	electrostatic discharge voltage	HBM; all pins; C = 250 pF; R = 1.5 k $\Omega$	8	kV

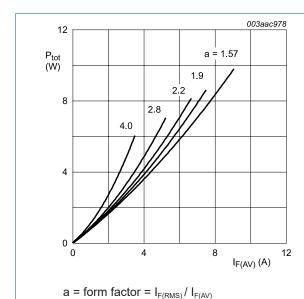


Fig. 1. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

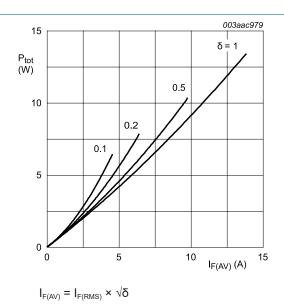


Fig. 2. Forward power dissipation as a function of average forward current; square waveform; maximum values

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## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to	with heatsink compound; both diodes conducting	-	-	1.6	K/W
	mounting base	with heatsink compound; per diode; <u>Fig 3</u>	-	-	2.4	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		-	60	-	K/W

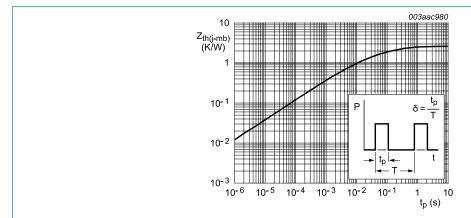


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse width

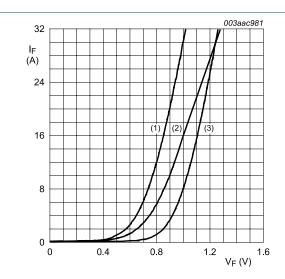
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## 10. Characteristics

### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics				,	
$V_{F}$	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>	-	0.72	0.85	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C	-	1	1.15	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 100 V; T <sub>j</sub> = 25 °C	-	6	30	μA
		V <sub>R</sub> = 100 V; T <sub>j</sub> = 100 °C	-	0.2	0.6	mA
Dynamic	characteristics					
Q <sub>r</sub>	recovered charge	$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}$	-	8	12.5	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A}/\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; ramp recovery; Fig. 5	-	20	25	ns
		$I_F$ = 0.5 A to $I_R$ = 1 A; $T_j$ = 25 °C; measured at $I_R$ = 0.25 A; step recovery; Fig. 6	-	10	20	ns
V <sub>FR</sub>	forward recovery voltage	$I_F = 1 \text{ A}$ ; $dI_F/dt = 10 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7	-	-	1	V

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(1) T<sub>j</sub> = 150 °C; typical values

(2)  $T_j = 150$  °C; maximum values

(3)  $T_j = 25$  °C; maximum values

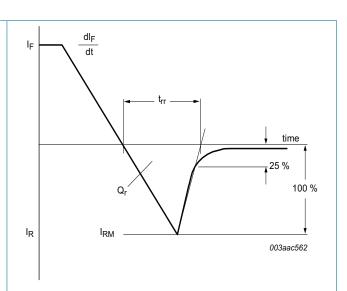
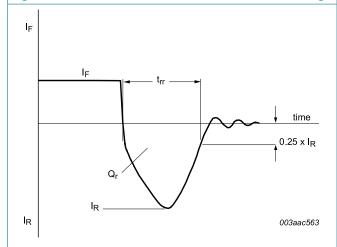


Fig. 5. Reverse recovery definitions; ramp recovery







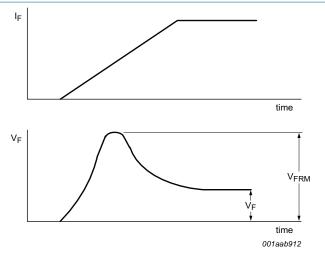


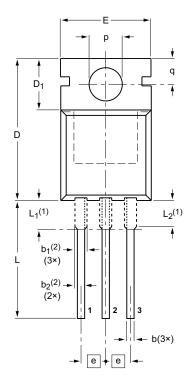
Fig. 7. Forward recovery definitions

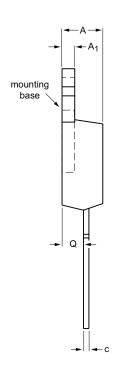
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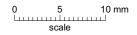
# 11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78







### **DIMENSIONS** (mm are the original dimensions)

UNIT	А	A <sub>1</sub>	b	b <sub>1</sub> <sup>(2)</sup>	b <sub>2</sub> <sup>(2)</sup>	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> <sup>(1)</sup>	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

#### Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

	REFER	EUROPEAN	ISSUE DATE		
IEC	JEDEC	JEITA		PROJECTION	1330E DATE
	3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13
	IEC	IEC JEDEC	IEC JEDEC JEITA	IEC JEDEC JEITA	IEC JEDEC JEITA PROJECTION

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# 12. Revision history

### **Table 8. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV32E-100 v.5	20180307	Product specification	-	BYV32E-100_4
Modifications:	Change from NXP vei	rsion to WeEn version		
BYV32E-100_4	20090302	Product specification	-	BYV32E_SERIES_3
Modifications:	guidelines of NXP S • Legal texts have be • Package outline upo	en adapted to the new compa	ny name where appro	opriate.
BYV32E_SERIES_3	20010301	Product specification	-	BYV32E_SERIES_2
BYV32E_SERIES_2	19980701	Product specification	-	BYV32EB_SERIES_1
BYV32EB_SERIES_1	19960801	Product specification	-	-

### Dual rugged ultrafast rectifier diode, 20 A, 100 V

## 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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